

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
13 January 2005 (13.01.2005)

PCT

(10) International Publication Number
WO 2005/004243 A1

(51) International Patent Classification⁷: **H01L 31/101**

(21) International Application Number:
PCT/IL2004/000573

(22) International Filing Date: 28 June 2004 (28.06.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
156744 2 July 2003 (02.07.2003) IL

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

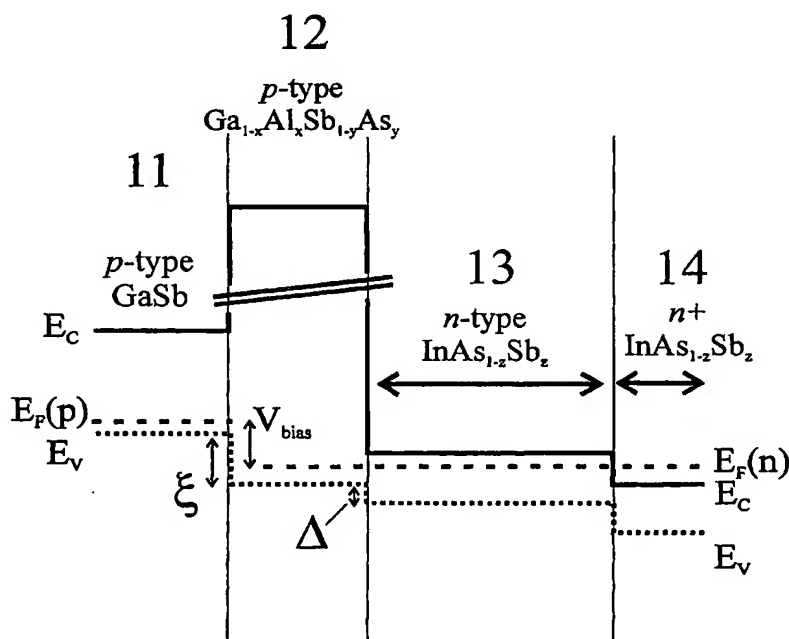
(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI,
SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

[Continued on next page]

(54) Title: DEPLETION-LESS PHOTODIODE WITH SUPPRESSED DARK CURRENT AND METHOD FOR PRODUCING
THE SAME



(57) Abstract: The invention relates to a photo-detector with a reduced G-R noise, which comprises a sequence of a p-type contact layer, a middle barrier layer and an n-type photon absorbing layer, wherein the middle barrier layer has an energy bandgap significantly greater than that of the photon absorbing layer, and there is no layer with a narrower energy bandgap than that in the photon-absorbing layer.



— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

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